



A Product Line of Diodes Incorporated

## **ZXTN2031F**

### **50V NPN MEDIUM POWER TRANSISTOR IN SOT23**

### **Features**

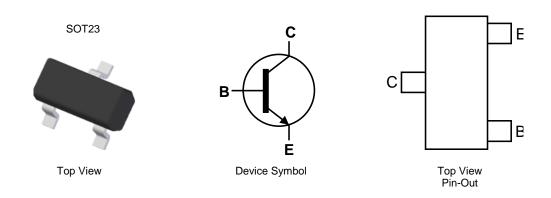
- $BV_{CEO} > 50V$
- BV<sub>CEV</sub> > 80V Forward Blocking Voltage
- I<sub>C</sub> = 5A high Continuous Collector Current
- I<sub>CM</sub> = 12A Peak Collector Current
- Low Saturation Voltage, V<sub>CE(SAT)</sub> < 40mV @1A
- $R_{CE(SAT)} = 24m\Omega$  for a Low Equivalent On-Resistance
- Complementary PNP Type: ZXTP2025F
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 03
- Weight 0.008 grams (Approximate)

### Applications

- MOSFET and IGBT Gate Driving
- Motor Drive
- Relay Lamp and Solenoid Drive
- DC-DC Converters



### Ordering Information (Note 4)

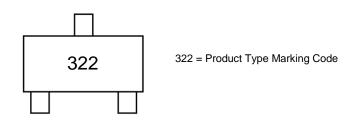
	Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel	
ZXTN2031FTA		AEC-Q101	322	7	8	3,000	
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.							

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

### **Marking Information**





### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	80	V
Collector-Emitter Voltage	V <sub>CEV</sub>	80	V
Collector-Emitter Voltage	V <sub>CEO</sub>	50	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	Ic	5	A
Peak Pulse Current	Ісм	12	A
Base Current	IB	1.2	A

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		1.0 8.0		
Power Dissipation Linear Derating Factor	(Note 6)	PD	1.2 9.6	W mW/°C	
	(Note 7)		1.56 12.5		
Thermal Resistance, Junction to Ambient	(Note 5) (Note 6)	R <sub>θJA</sub>	125 104	°C/W	
	(Note 7)	1 VOJA	80		
Thermal Resistance, Junction to Lead	(Note 8)	R <sub>θJL</sub>	57	°C/W	
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C		

### ESD Ratings (Note 9)

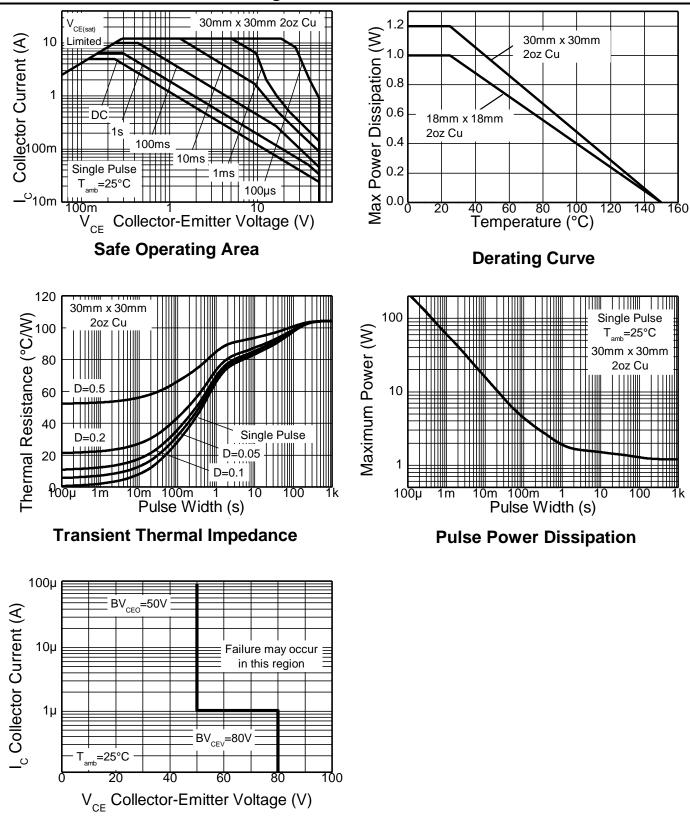
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

Notes: 5. For a device mounted with the collector lead on 18mm x 18mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air For a device mounted with the collector lead on 18mm x 18mm 202 copper that is conditions whilst operating in steady-state.
Same as note (5), except the device is mounted on 30mm x 30mm 202 copper.
Same as note (6), except measured at t < 5 seconds.</li>
Thermal resistance from junction to solder-point (at the end of the collector lead).
Refer to JEDEC specification JESD22-A114 and JESD22-A115.



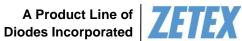






Safe Operating Area





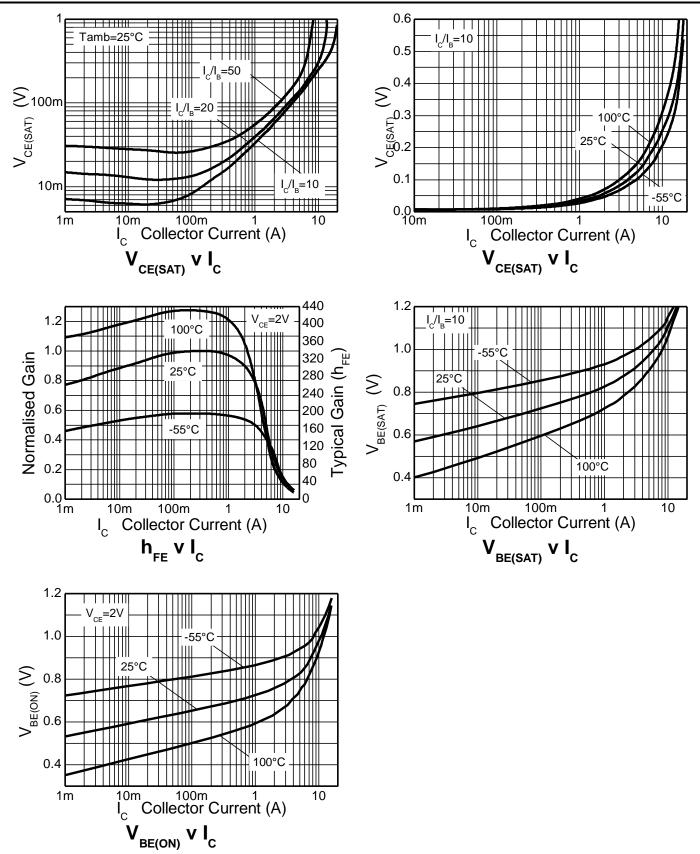
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	80	175	-	V	$I_{\rm C} = 100 \mu {\rm A}$
Collector-Emitter Breakdown Voltage	BV <sub>CEV</sub>	80	175	-	V	$I_{C} = 1\mu A$ , $-1V < V_{BE} < +0.3V$
Collector-Emitter Breakdown Voltage (Note 10)	BV <sub>CEO</sub>	50	75	-	V	$I_{\rm C} = 10 {\rm mA}$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	8.3	-	V	I <sub>E</sub> = 100μA
Collector – Emitter Cut-Off Current	ICEV	-	<1	20	nA	$V_{CE} = 60V, V_{BE} = -1V$
Collector - Base Cut-Off Current	ICBO	-	<1	20	nA	$V_{CB} = 60V$
Emitter Cut-off Current	I <sub>EBO</sub>	-	<1	10	nA	$V_{EB} = 6V$
Static Forward Current Transfer Ratio (Note 10)	hfe	190 200 200 80	300 350 340 125	- 560 - -	-	$I_{C} = 10mA, V_{CE} = 2V$ $I_{C} = 500mA, V_{CE} = 2V$ $I_{C} = 2A, V_{CE} = 2V$ $I_{C} = 5A, V_{CE} = 2V$
Collector-Emitter Saturation Voltage (Note 10)	V <sub>CE(sat)</sub>	-	13 30 80 135	18 40 110 170	mV	$\begin{split} I_{C} &= 100 \text{mA}, \ I_{B} = 5 \text{mA} \\ I_{C} &= 1 \text{A}, \ I_{B} = 100 \text{mA} \\ I_{C} &= 2 \text{A}, \ I_{B} = 40 \text{mA} \\ I_{C} &= 5 \text{A}, \ I_{B} = 250 \text{mA} \end{split}$
Base-Emitter Saturation Voltage (Note 10)	V <sub>BE(sat)</sub>	-	800 920	900 1000	mV	$I_{C} = 2A, I_{B} = 40mA$ $I_{C} = 5A, I_{B} = 250mA$
Base-Emitter Turn-On Voltage (Note 10)	V <sub>BE(on)</sub>	-	830	930	mV	$I_{C} = 5A, V_{CE} = 2V$
Transition Frequency	FT	-	125	-	MHz	I <sub>C</sub> = 500mA, V <sub>CE</sub> = 10V, f=50MHz
Output Capacitance	Cobo	-	29	-	pF	$V_{CB} = 10V$ , f=1MHz
Delay Time	t <sub>(d)</sub>	-	16	-	ns	
Rise Time	t <sub>(r)</sub>	-	27	-	ns	V <sub>CC</sub> = 12V, I <sub>C</sub> = 2.5A,
Storage Time	t <sub>(stg)</sub>	-	468	-	ns	I <sub>B1</sub> = - I <sub>B1</sub> = 125mA
Fall Time	t <sub>(f)</sub>	-	44	-	ns	

10. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2% Note:





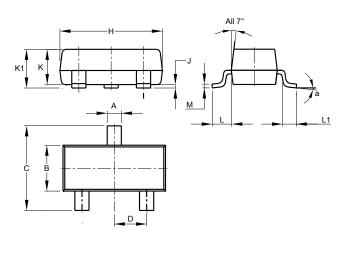




EX

## **Package Outline Dimensions**

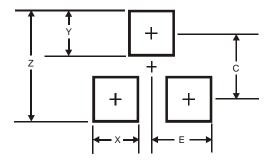
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
Μ	0.085	0.150	0.110			
а	<b>a</b> 8°					
All Dimensions in mm						

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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